15 Nov. (Thursday)

	Room A	Room B	Room C
	15Aa1 Surface/Interface Structures & Properties-Physical Properties-	15Ba1 Molecular Assembly & Self-organization	15Ca1 Characterization & Instrumentation
9:00	15Aa1-1,2 Manipulating the Spins of Single Molecules (Invited) Qi-Kun Xue, Beijing , China	15Ba1-1,2 Nanoscience at Silicon Carbide Surfaces: Selective Metallization/Passivation and Metal Atom Pair & Atomic Wire Nano-objects (Invited) Patrick Soukiassian, Gif sur Yvetter, France	15Ca1-1,2 Application of a Single-Atom Electron Source to Scanning Electron Microscope (Invited) Chuhei Oshima, Tokyo, Japan
	15Aa1-3 Direct observation of spin splitting in surface states of non-magnetic Bi Toru Hirahara, Tokyo, Japan	15Ba1-3 Microscopic work function measurements of C60 thin films by means of scanning tunneling microscopy Masashi Shimura, Tsukuba, Japan	15Ca1-3 On the role of halide ions in single molecule SERS Masayuki Futamata, Tsukuba, Japan
	15Aa1-4 Growth and magnetism of pristine Fe films on GaAs(001) Jae-Sung Kim, Seoul, Korea (Rep. of)	15Ba1-4 Mechanisms of chiral recognition revealed at the single molecule level Giovanni Costantini, Stuttgart, Germany	15Ca1-4 Atomic Level Analysis of Imidazolium-Based Ionic Liquids by the Scanning Atom Probe Osamu Nishikawa, Nonoichi, Japan
10:00	15Aa1-5 Probing the parity of substrate bulk bands by quantum-well states Denis Vyalikh, Dresden, Germany	15Ba1-5 Adsorption structure and work function of dicarboxylic acid on Cu (110) surface Shinjiro Yagyu, Tsukuba, Japan	15Ca1-5 Cs-corrected STEM studies of Ge nanodots grown on Si(001) surfaces with an ultrathin SiO2 coverage Nobuo Tanaka, Nagoya, Japan
	15Aa2 Surf./Interface Structures & Properties-Compound Semiconductors-	15Ba2 Molecular Assembly & Organic Thin film	15Ca2 Characterization & Instrumentation
	15Aa2-1,2 in-situ STM observation on III-V compound semiconductor surfaces during Molecular Beam Epitaxy growth (Invited) Shiro Tsukamoto, Anan, Japan	15Ba2-1 Tuning the Intermolecular Distances in Self-Assembled Monolayers of Bipyridine Derivatives Yoshihiro Kikkawa, Tsukuba, Ibaraki, Japan 15Ba2-2 Nanoscopic deformation of an annealed nafion film studied by atomic force microscopy Kazuo Umemura, Tokyo, Japan	15Ca2-1,2 Correlation between the Electronic Structure of Working Catalyst Surfaces and the Selectivity of Heterogeneous Catalytic Reactions (Invited) Axel Knop-Gericke, Berlin, Germany
11:00	15Aa2-3 Formation of multiple nanoscale twin boundaries acting as twinning superlattice in AlGaAs epilayers Yutaka Ohno, Sendai, Japan	15Ba2-3 Growth and Transistor Property of Quaterrylene Thin Film on SiO2 Surface Using Ultra-Low Flux Rate System Ryoma Hayakawa, Tsukuba, Japan	15Ca2-3 Temperature Dependence Characterization of Metal-Insulator-Nonuniformly Doped Semiconductor Solar Cell M.Abdel-Gawad El-Sayed, Assiut, Egypt
	15Aa2-4 P-rich InP(001)-(2x1) Surface Structure in MOCVD Gaseous Ambient Using Grazing Incidence X-ray Diffraction Seiji Fujikawa, Ako-gun, Japan	15Ba2-4 Programmable Nonvolatile Memory Devices Based on the Polymeric Blends of Metal Nanoparticles as Charge Storage Media Jang-Sik Lee, Seoul, South Korea	15Ca2-4 Detection of Sulfur from Ni(110) Surface using by Electron-Stimulated Desorption Spectroscopy Kazuyuki Ueda, Nagoya, Japan
	15Aa2-5 Growth of InAs nanowires on Si(111) by selective-area MOVPE Katsuhiro Tomioka, sapporo, Japan	15Ba2-5Observation and Controlling of Metal Growth on Functionalized Alkanethiolate Self-Assembled Monolayers Masato Maitani, University Park, PA, USA	15Ca2-5 First-Principles Study of Epitaxial Silicon Oxynitride Layer on a SiC Surface Yasunobu Ando, Tokyo, Japan
	15Aa2-6 An ab initio-based approach to phase diagram calculations for GaN(0001) surfaces Tomonori Ito, Tsu, Japan	15Ba2-6 Surface modification of self assembling monolayers bearing photosensitive aromatic esters Thomas Griesser, Graz, Austria	15Ca2-6 Visualization of current pathways in depleted regions of Si pn junctions under scanning tunneling microscope observation Shigehiko Hasegawa, Ibaraki, Japan
12:00	15Aa2-7 Structural phases of ultrathin Si/Cu(111) films J.S. Tsay, Taipei, Taiwan	15Ba2-7 Self-assembling of supported lipid bilayer patterns on sapphire surfaces Toshinari Isono, Yokohama, Japan	
	Lunch		
13:00	15Ap Surf./Interface Structures & Properties-Si and Related Semiconductors	15Bp Nano-Electronics & Devices	
13:30	15Ap-1,2 Topographic and electronic properties of metallic atomic chains on vicinal Si surfaces (Invited) Mieczyslaw Jalochowski, Lublin, Poland	15Bp-1,2 Kinetic Factors in VLS Growth of Si and Ge Nanowires (Invited) Jerry Tersoff, Blauvelt, NY, USA	
14:00	15Ap-3 Quasi-one dimensional structures on the Si(111) surface induced by Ba adsorption Geunseop Lee, Inchon, Republic of Korea	15Bp-3 Integration of Individual Nanoscale Structures into Devices using Dynamic Nanostenciling Stefan Egger, Tsukuba, Ibaraki, Japan	
	15Ap-4 Electronic and optical properties of ultrahigh density Ge1-xSnx quantum dots Yoshiaki Nakamura, Tokyo, Japan	15Bp-4 Multi-value transistor by self-assemble molecular nanowires Yutaka Wakayama, Tsukuba, Japan	
	15Ap-5 Formations and Stability of Misfit Dislocation in Ge on Si(001) Yoshitaka Fujimoto, baraki, Japan	15Bp-5,6 Controlling Interface Properties of Silicide/Si Contacts for Si ULSI Applications (Invited) Shigeaki Zaima, Nagoya, Japan	
	15Ap-6 Origin of defects at the nonpolar 4H-AlN(11-20)/4H-SiC(11-20) interface revealed by TEM observations Masahiro Horita, Kyoto, Japan		
15:00	15Ap-7 Subband dispersion in Si(111) inversion layer induced by Si(111)4x1-In measured by ARPES Masaaki Yoshikawa, Ikoma, Japan	15Bp-7 Probing the surface potential of Si inversion layers through quantum levels Sakura Nishino Takeda, Nara, Japan	
	15Ap-8 Surface restructuring process on a Ag/Ge(001) surface studied by photoelectron spectroscopy Kan Nakatsuji, Kashiwa, Japan	15Bp-8 Influence of Initial Surface Reconstruction on the Interface Structure of HfO2/GaAs Tetsuji Yasuda, Tsukuba, Japan	
	Closing Ceremony		